

YJ Planar Schottky Barrier Diode Die Specification

100V 30A, 122mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB122S100AS-290A

Main Products Characterstics

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	100 V
Average forward current		
		-50 to +175 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol
Reverse breakdown voltage $I_R = 1mA$	V_{BR}
$I_F = 15A$	
	$\leq 2\%$
Maximum reverse current $V_R = V_{RRM}$	I_R
	$\leq 2\%$

Device Schematics and Outline Drawing

Die Thickness *	
Die Size **	122 Mils
Top Metal Pad	
Active Area	
Top Metal	
Back Metal	
Note: 1 * :	Also can offer device with 8 mils thickness
2 **:	Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
YangjieElectronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.	Store in original container, in dessicated nitrogen, with no contamination.
Data sheet information is subjected to change without notice.	Shelf life for parts stored in above condition is 2 years.
	If the storage is done in normal atmosphere shelf life is reduced to 6 months.